

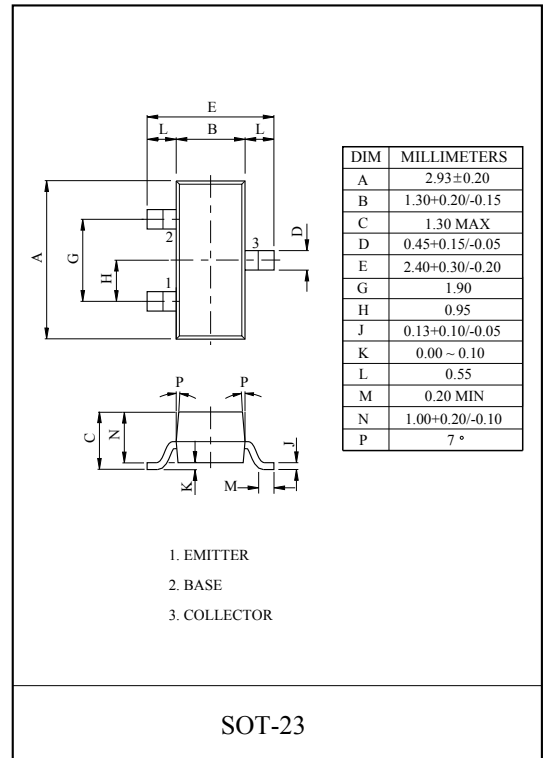
HIGH VOLTAGE APPLICATION.
TELEPHONE APPLICATION.

FEATURES

- Complementary to MMBTA92/93.

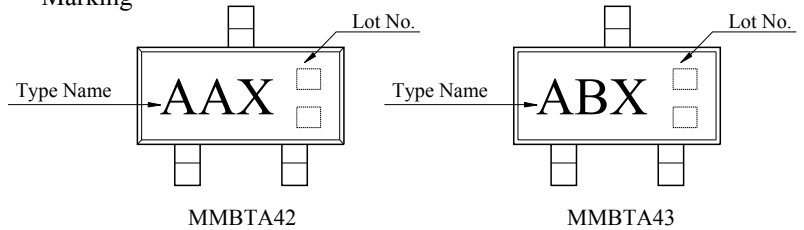
MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage	MMBTA42	V_{CBO}	300	V
	MMBTA43		200	
Collector-Emitter Voltage	MMBTA42	V_{CEO}	300	V
	MMBTA43		200	
Emitter-Base Voltage		V_{EBO}	5.0	V
Collector Current		I_C	500	mA
Emitter Current		I_E	-500	mA
Collector Power Dissipation		P_C^*	350	mW
Junction Temperature		T_j	150	°C
Storage Temperature		T_{stg}	-55 ~ 150	°C



* : Package Mounted On 99.5% Alumina 10×8×0.6mm.

Marking



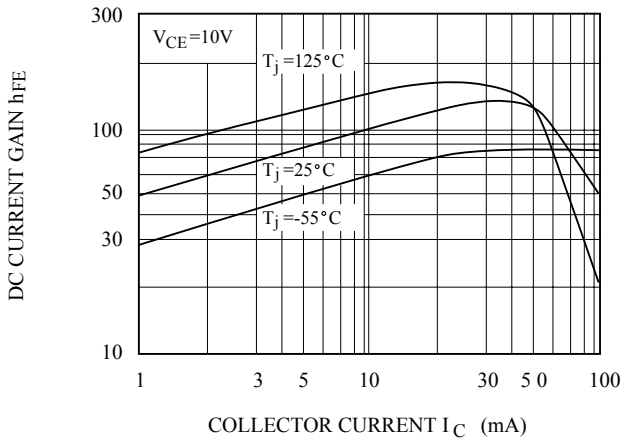
ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	MMBTA42	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	300	-	-	V
	MMBTA43			200	-	-	
Collector-Emitter Breakdown Voltage	MMBTA42	$V_{(BE)CEO}$	$I_C=1.0mA, I_B=0$	300	-	-	V
	MMBTA43			200	-	-	
DC Current Gain	* h_{FE}		$I_C=1.0mA, V_{CE}=10V$	40	-	-	
			$I_C=10mA, V_{CE}=10V$	40	-	-	
			$I_C=30mA, V_{CE}=10V$	40	-	-	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C=20mA, I_B=2.0mA$	-	-	0.5	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C=20mA, I_B=2.0mA$	-	-	0.9	V
Transition Frequency		f_T	$V_{CE}=20V, I_C=10mA, f=100MHz$	50	-	-	MHz
Collector Output Capacitance	MMBTA42	C_{ob}	$V_{CB}=20V, I_E=0, f=1MHz$	-	-	3.0	pF
	MMBTA43			-	-	4.0	

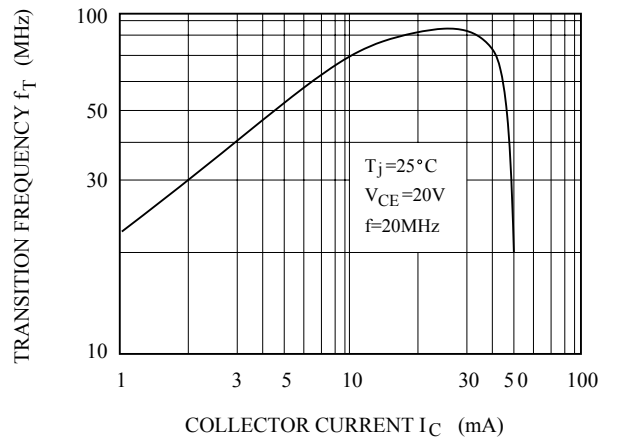
*Pulse Test : Pulse Width ≤ 300μS, Duty Cycle ≤ 2.0%

MMBTA42/43

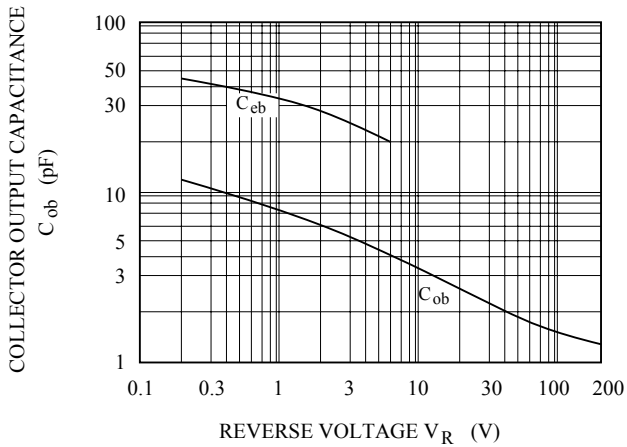
$h_{FE} - I_C$



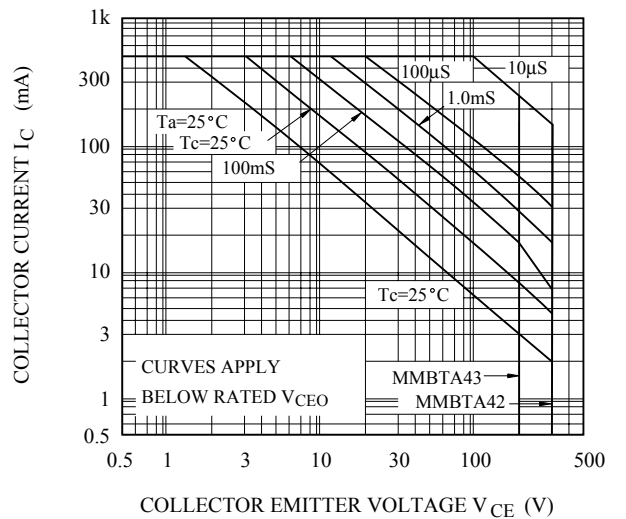
$f_T - I_C$



$C_{ob} - V_R$



$I_C - V_{CE}$



$V_{BE(sat)}, V_{CE(sat)} - I_C$

